

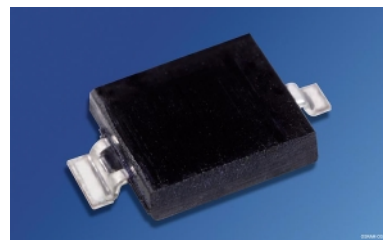
# Silizium-Pin-Fotodiode mit Tageslichtsperrfilter; in SMT

## Silicon Pin Photodiode with Daylight Filter; in SMT

**BP 104 F**  
**BP 104 FS**



BP 104 F



BP 104 FS

### Wesentliche Merkmale

- Speziell geeignet für Anwendungen bei 950 nm
- Kurze Schaltzeit (typ. 20 ns)
- DIL-Plastikbauform mit hoher Packungsdichte
- BP 104 FS: geeignet für Vapor-Phase Löten und IR-Reflow Löten

### Anwendungen

- IR-Fernsteuerung von Fernseh- und Rundfunkgeräten, Videorecordern, Lichtdimmern, Gerätefernsteuerungen
- Lichtschranken für Gleich- und Wechsellichtbetrieb

### Features

- Especially suitable for applications of 950 nm
- Short switching time (typ. 20 ns)
- DIL plastic package with high packing density
- BP 104 FS: suitable for vapor-phase and IR-reflow soldering

### Applications

- IR remote control of hi-fi and TV sets, video tape recorders, dimmers, remote controls of various equipment
- Photointerrupters

Typ Type	Bestellnummer Ordering Code	Gehäuse Package
BP 104 F	Q62702-P84	DIL-Gehäuse, schwarzes Epoxy-Gießharz, Kathodenkennzeichnung: Fähnchen am Anschluß DIL package, black epoxy resin Cathode marking: flag on lead
BP 104 FS	Q62702-P1646	DIL/SMT-Gehäuse, schwarzes Epoxy-Gießharz, Kathodenkennzeichnung: Langer, breiter Anschluß DIL/SMT package, black epoxy resin Cathode marking: long broad lead

**Grenzwerte**  
**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 100	°C
Sperrspannung Reverse voltage	$V_R$	20	V
Verlustleistung, $T_A = 25\text{ °C}$	$P_{tot}$	150	mW

**Kennwerte ( $T_A = 25\text{ °C}$ ,  $\lambda = 950\text{ nm}$ )**  
**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Fotostrom Photocurrent $V_R = 5\text{ V}$ , $E_e = 1\text{ mW/cm}^2$	$I_P$	34 ( $\geq 25$ )	$\mu\text{A}$
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	950	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von $S_{\text{max}}$ Spectral range of sensitivity $S = 10\%$ of $S_{\text{max}}$	$\lambda$	800 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	$A$	4.84	$\text{mm}^2$
Abmessung der bestrahlungsempfindlichen Fläche Dimensions of radiant sensitive area	$L \times B$ $L \times W$	$2.20 \times 2.20$	$\text{mm} \times \text{mm}$
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	$H$	0.5 0.3 (BP 104 FS)	mm
Halbwinkel Half angle	$\varphi$	$\pm 60$	Grad deg.
Dunkelstrom, $V_R = 10\text{ V}$ Dark current	$I_R$	2 ( $\leq 30$ )	nA
Spektrale Fotoempfindlichkeit Spectral sensitivity	$S_\lambda$	0.70	A/W
Quantenausbeute Quantum yield	$\eta$	0.90	<u>Electrons</u> Photon

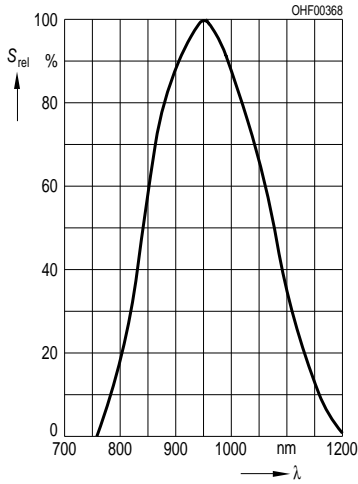
Kennwerte ( $T_A = 25\text{ °C}$ ,  $\lambda = 950\text{ nm}$ )

Characteristics (cont'd)

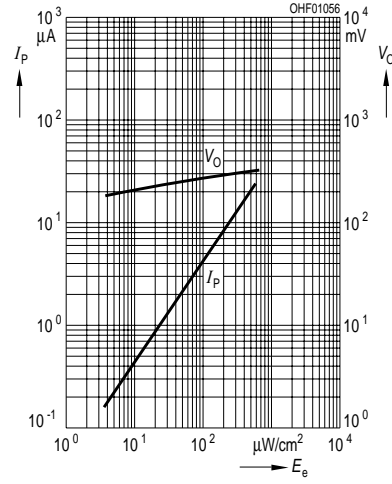
Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Leerlaufspannung, $E_e = 0.5\text{ mW/cm}^2$ Open-circuit voltage	$V_O$	330 ( $\geq 250$ )	mV
Kurzschlußstrom, $E_e = 0.5\text{ mW/cm}^2$ Short-circuit current	$I_{SC}$	17	$\mu\text{A}$
Anstiegs- und Abfallzeit des Fotostromes Rise and fall time of the photocurrent $R_L = 50\ \Omega$ ; $V_R = 5\text{ V}$ ; $\lambda = 850\text{ nm}$ ; $I_p = 800\ \mu\text{A}$	$t_r, t_f$	20	ns
Durchlaßspannung, $I_F = 100\text{ mA}$ , $E = 0$ Forward voltage	$V_F$	1.3	V
Kapazität, $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$ Capacitance	$C_0$	48	pF
Temperaturkoeffizient von $V_O$ Temperature coefficient of $V_O$	$TC_V$	-2.6	mV/K
Temperaturkoeffizient von $I_{SC}$ Temperature coefficient of $I_{SC}$	$TC_I$	0.18	%/K
Rauschäquivalente Strahlungsleistung Noise equivalent power $V_R = 10\text{ V}$	$NEP$	$3.6 \times 10^{-14}$	$\frac{\text{W}}{\sqrt{\text{Hz}}}$
Nachweisgrenze, $V_R = 10\text{ V}$ Detection limit	$D^*$	$6.1 \times 10^{12}$	$\frac{\text{cm} \times \sqrt{\text{Hz}}}{\text{W}}$

**Relative Spectral Sensitivity**

$S_{rel} = f(\lambda)$

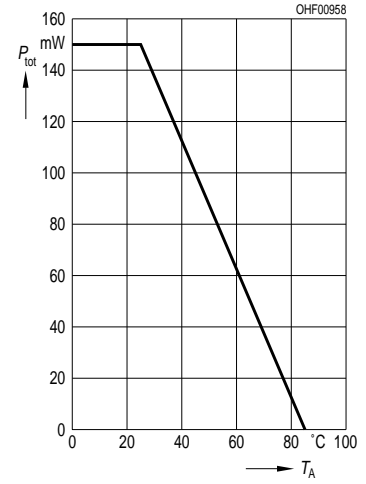


**Photocurrent  $I_P = f(E_e)$ ,  $V_R = 5 V$   
Open-Circuit Voltage  $V_O = f(E_e)$**



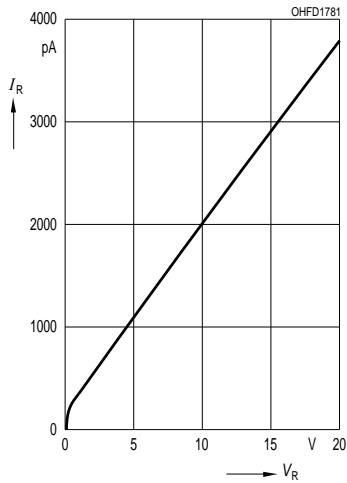
**Total Power Dissipation**

$P_{tot} = f(T_A)$



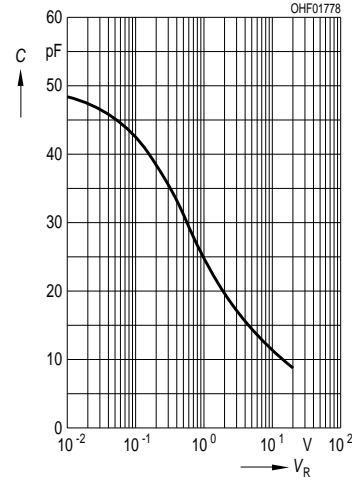
**Dark Current**

$I_R = f(V_R), E = 0$



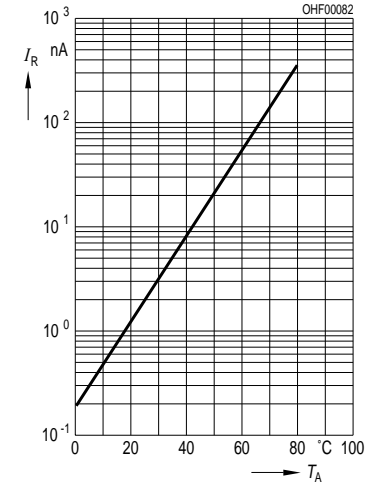
**Capacitance**

$C = f(V_R), f = 1 MHz, E = 0$



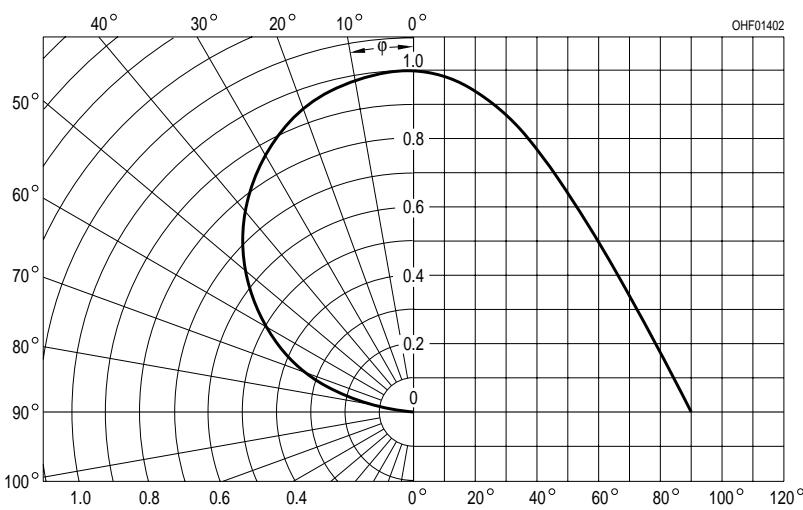
**Dark Current**

$I_R = f(T_A), V_R = 10 V, E = 0$

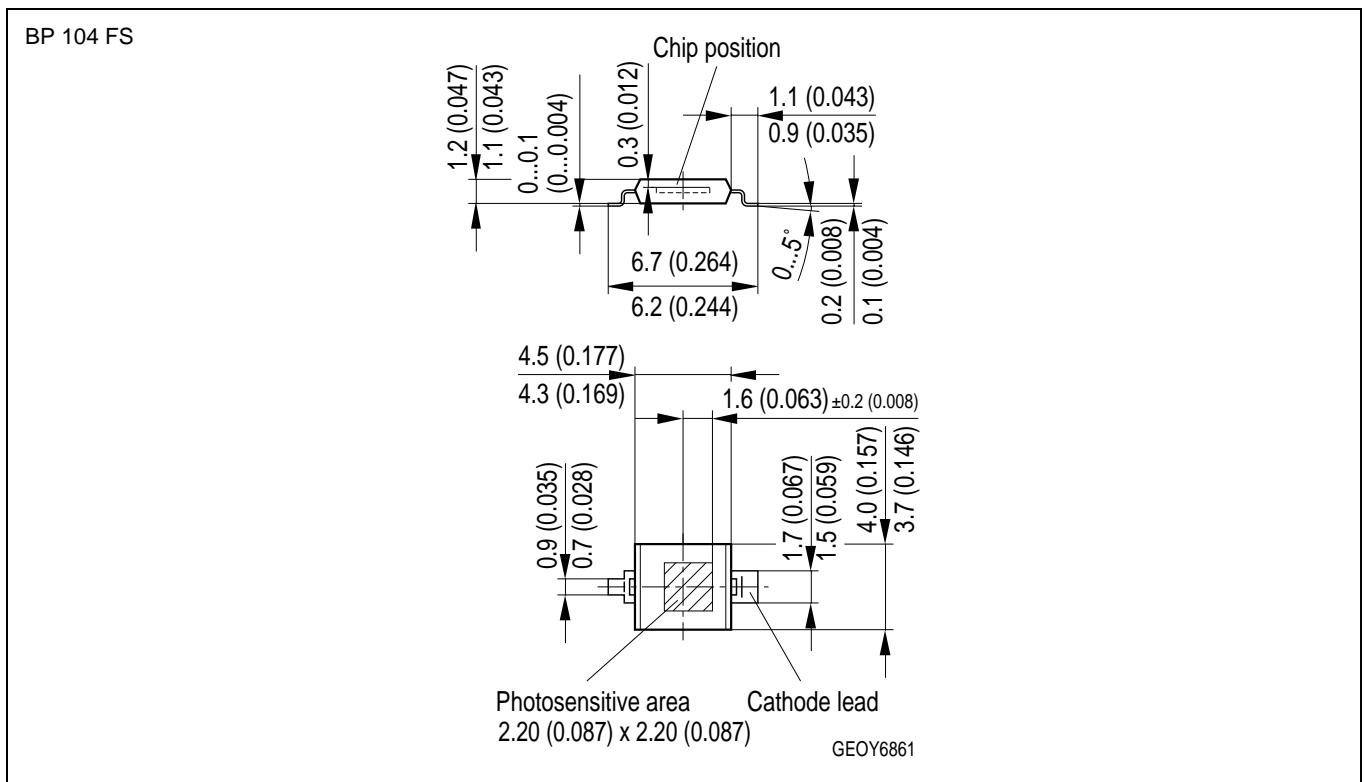
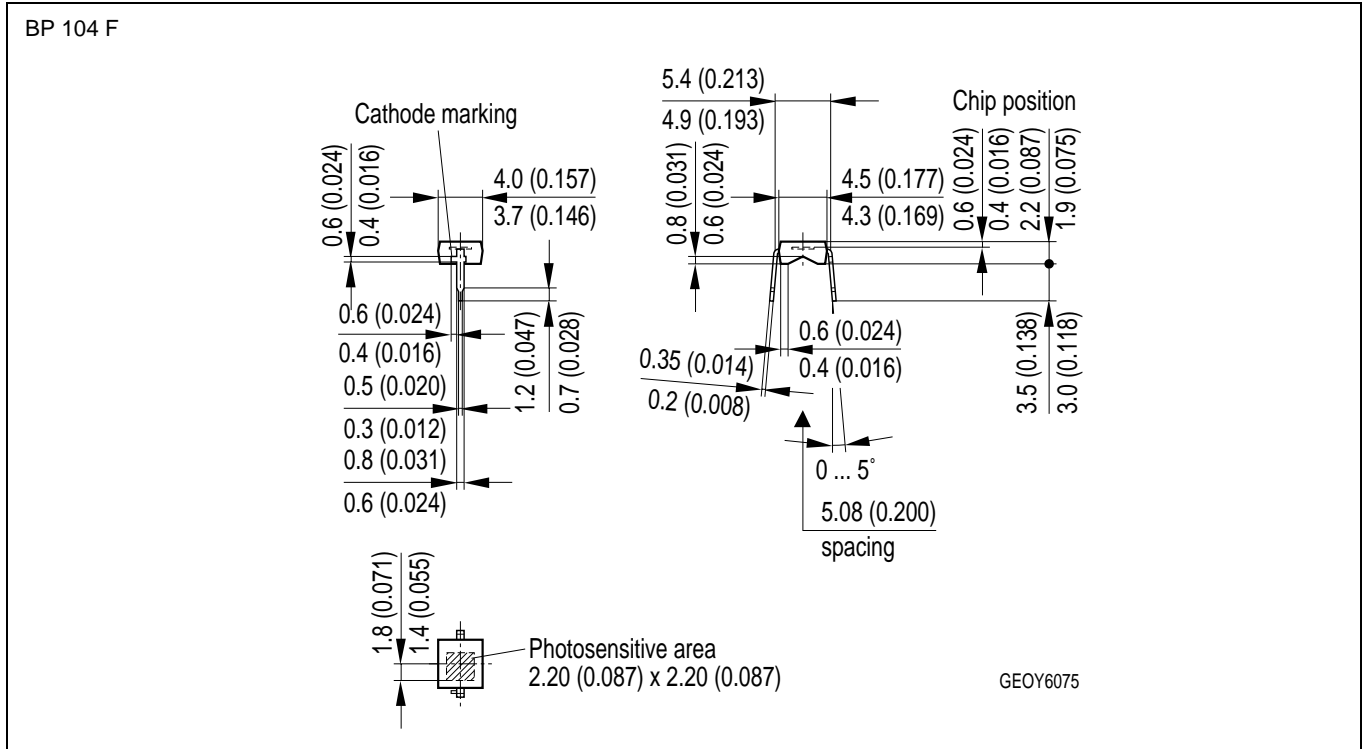


**Directional Characteristics**

$S_{rel} = f(\phi)$



Maßzeichnung  
Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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